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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

/PD/	Sakamoto et al, "Formation of Anodic Reaction Film on n-type Si", Applied Physics, vol. 44, Issue No. 5, 1975, pp.497-506
	Tokuyama, "Comprehensive Treatise on Electronics Technology", Vol. 3, MOS Device, Kogyochosakai, 1976, pp.124-126
	Asusa et al, "Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density Formed by Chemical Oxidation of Si", Applied Physics Letters, Vol. 81, No. 18, 28 October 2002, pp. 3410-3412
↓	Kobayashi et al, "Nitric Acid Oxidation of Si to Form Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density", Journal of Applied Physics, Vol. 94, No. 11, American Institute of Physics, 2003, pp. 7328-7335
/PD/	Asuha et al, "Low Temperature Formation of SiO ₂ /Si Structure by Chemical Method and Spectroscopic Observation", Meeting Abstracts of the Physical Society of Japan, Vol. 58, Issue 2, Part 4, Meeting Abstracts, 2003, pp. 771-

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/Phuc Dang/

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